

## P-Channel Enhancement Mode Power MOSFET

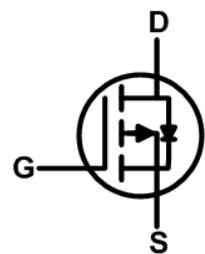
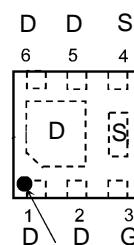
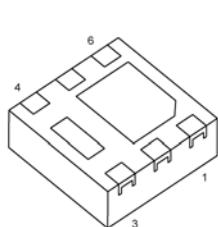
### ● Features

$V_{DS} = -30V$

$I_D = -10A$

$R_{DS(ON)} \leq 21m\Omega (V_{GS} = -10V)$

### ● Pin Configurations



Polarity marking (on the top)

\*Electrodes : on the bottom

### ● General Description

The TPM2030JX is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The TPM2030JX meet the RoHS and Green Product requirement.

### ● Package Marking and Ordering Information

Product	Package	Marking	Packing
TPM2030JX	DFN2X2-6L	1003 XXYY	3000pcs. /7" Reel

### ● Absolute Maximum Ratings (@TA=25°C unless otherwise noted)

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		$V_{DSS}$	-30	V
Gate Source Voltage		$V_{GSS}$	$\pm 20$	V
Drain Current (Continuous) *AC	TA=25°C	$I_D$	-10	A
	TA=100°C		-8	
Drain Current (Pulse) *B		$I_{DM}$	-30	A
Power Dissipation	TA=25°C	$P_D$	2.8	W
Operating Temperature/ Storage Temperature		$T_J/T_{STG}$	-55~150	°C
Thermal Resistance ,Junction-to-Ambient		$R_{\theta JA}$	50	°C/W

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● **Electrical Characteristics (@TA=25°C unless otherwise noted)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	--	--	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	--	--	-1	uA
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250uA	-1.0	--	-2.5	V
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	--	--	±100	nA
Drain-Source On-state Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-8A	--	--	21	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6A	--	--	34	mΩ
Diode Forward Voltage	V <sub>SD</sub>	I <sub>SD</sub> =-1A, V <sub>GS</sub> =0V	--	--	-1.0	V
<b>Switching</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-8A	--	12	--	nC
Gate- Source Charge	Q <sub>gs</sub>		--	1.8	--	nC
Gate- Drain Charge	Q <sub>gd</sub>		--	3	--	nC
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, R <sub>GEN</sub> =3Ω, R <sub>L</sub> =1.8Ω	--	7.7	--	ns
Turn-on Rise Time	t <sub>r</sub>		--	5.5	--	ns
Turn-off Delay Time	t <sub>d(off)</sub>		--	26.3	--	ns
Turn-off Fall Time	t <sub>f</sub>		--	11.5	--	ns
<b>Dynamic</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHZ	--	530	--	pF
Output Capacitance	C <sub>oss</sub>		--	114	--	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		--	75	--	pF

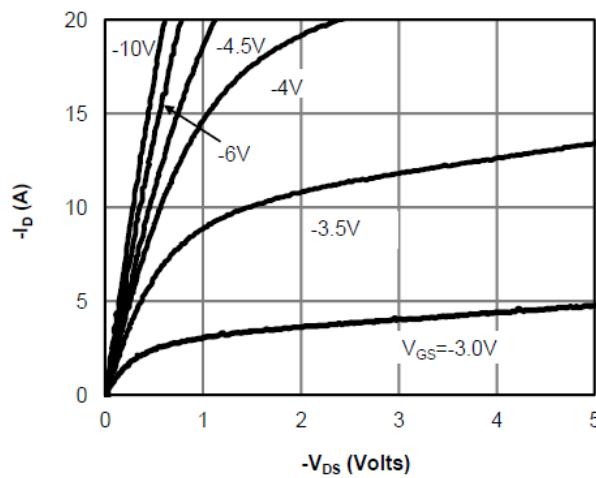
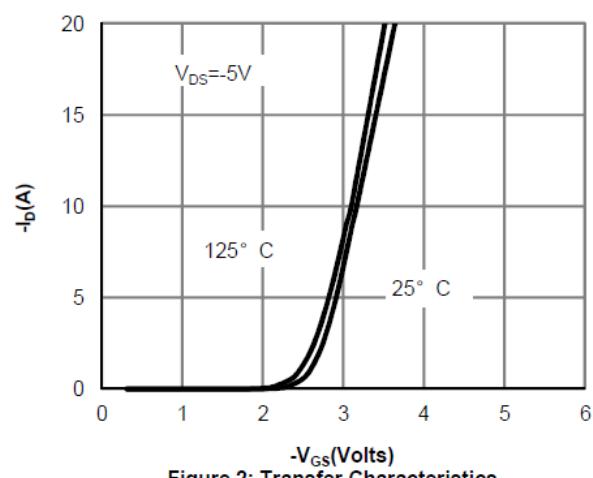
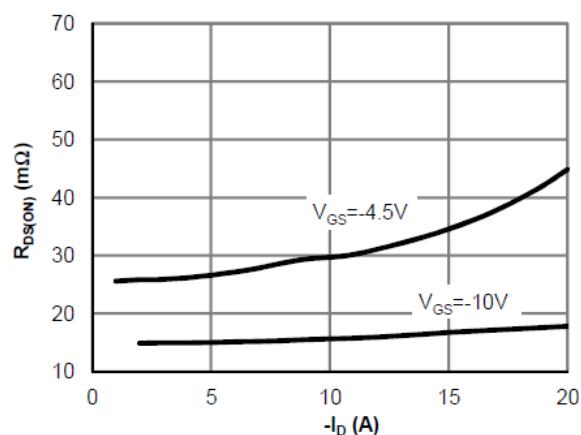
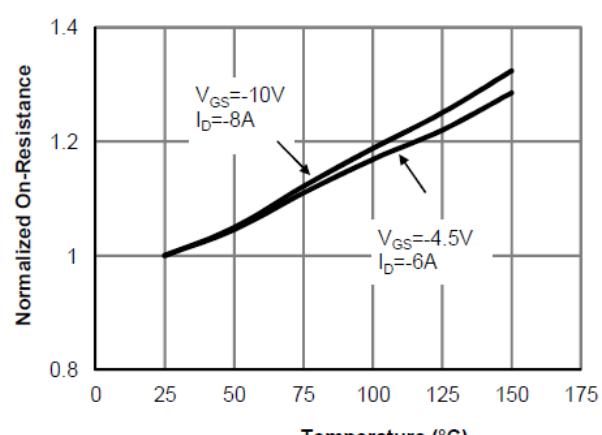
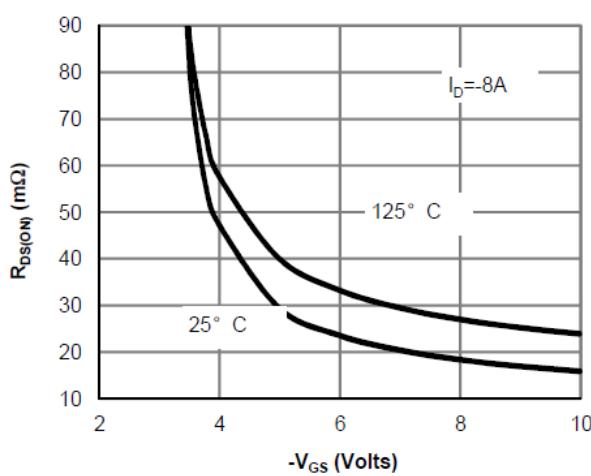
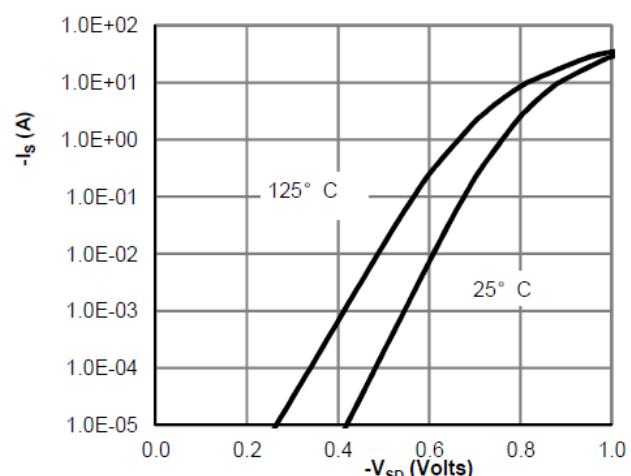
A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in2 FR- 4 board with 2oz. Copper, in a still air environment with TA=25C. The value in any given

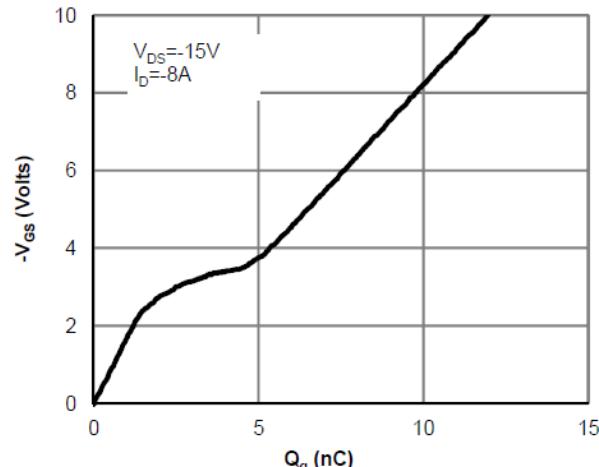
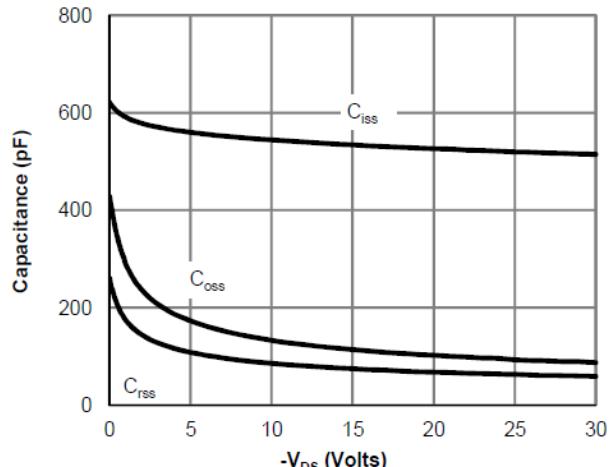
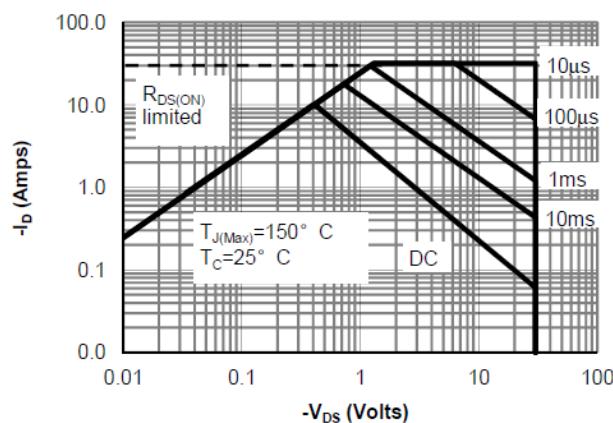
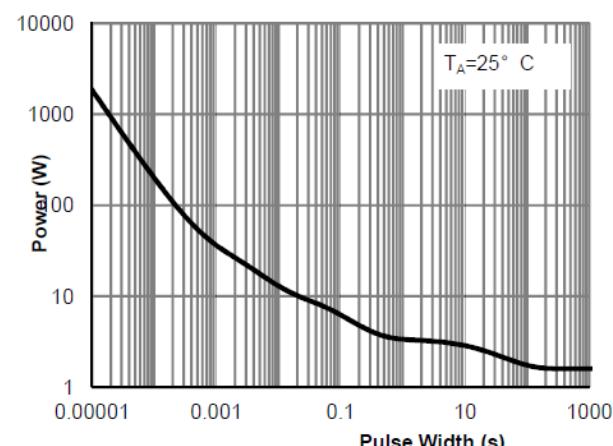
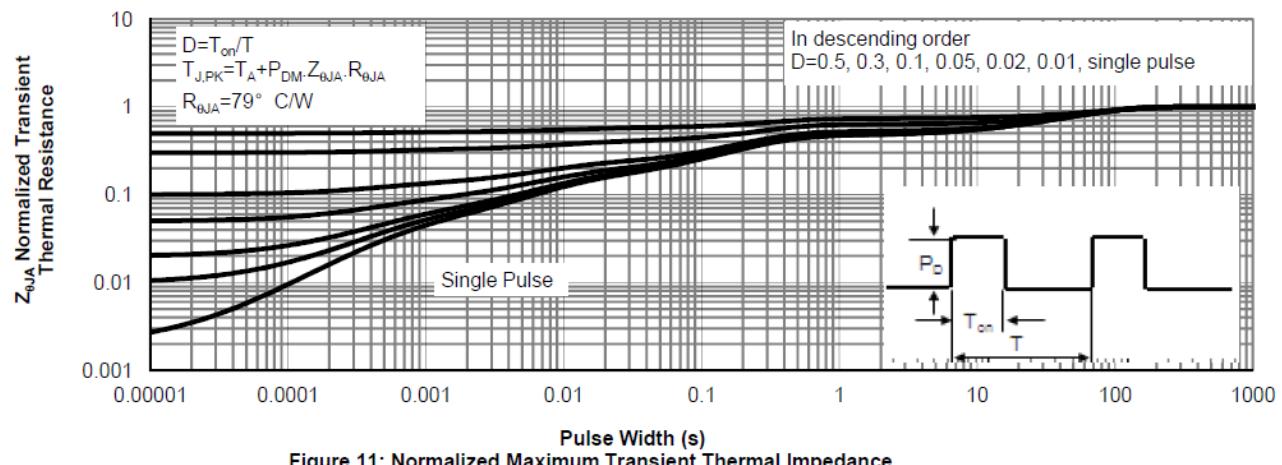
application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature .

C: The current rating is based on the t< 10s junction to ambient thermal resistance rating.

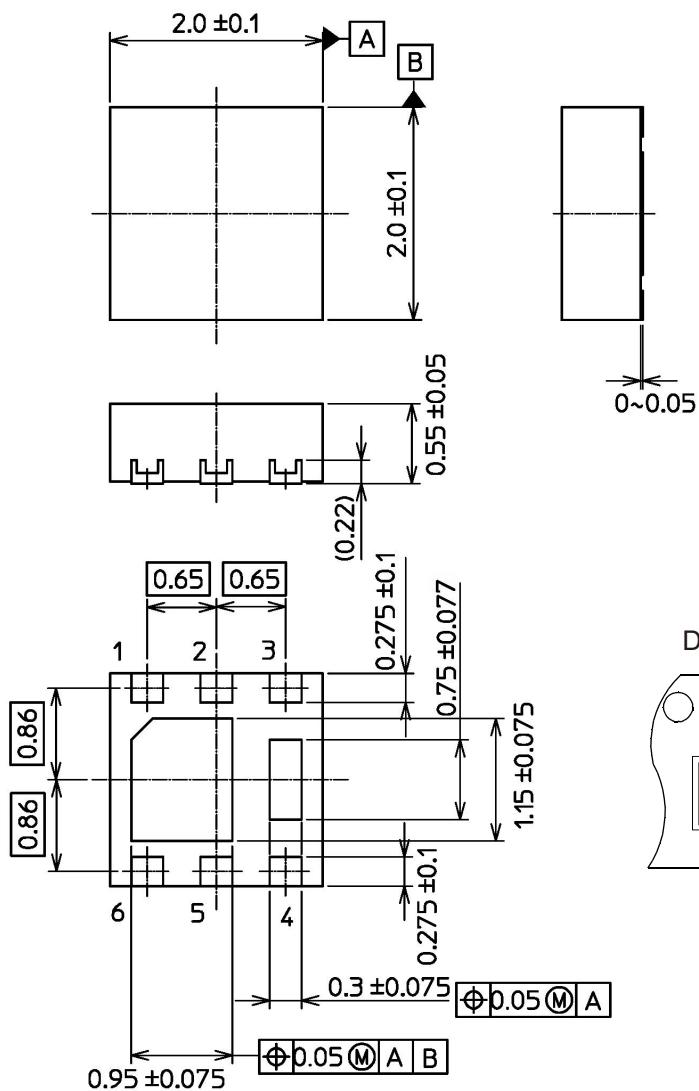
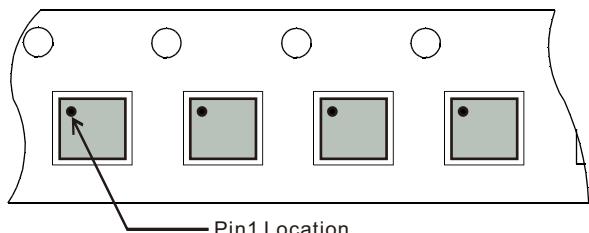
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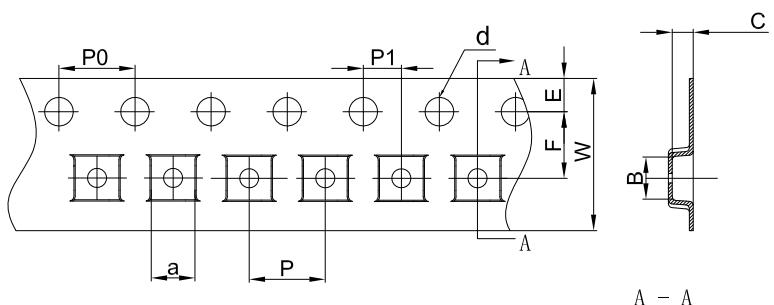
● **TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

**Fig 1: On-Region Characteristics**

**Figure 2: Transfer Characteristics**

**Figure 3: On-Resistance vs. Drain Current and Gate Voltage**

**Figure 4: On-Resistance vs. Junction Temperature**

**Figure 5: On-Resistance vs. Gate-Source Voltage**

**Figure 6: Body-Diode Characteristics**

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**Figure 7: Gate-Charge Characteristics**

**Figure 8: Capacitance Characteristics**

**Figure 9: Maximum Forward Biased Safe Operating Area**

**Figure 10: Single Pulse Power Rating Junction-to-A**

**Figure 11: Normalized Maximum Transient Thermal Impedance**

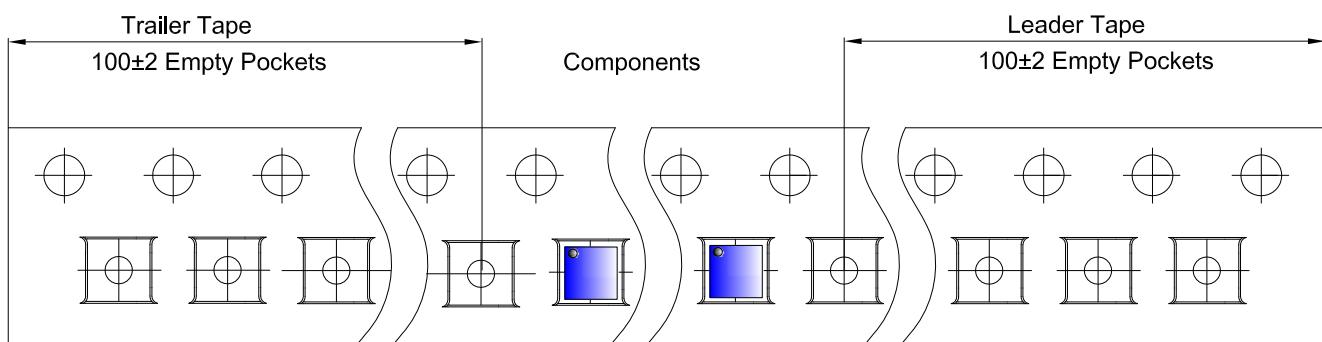
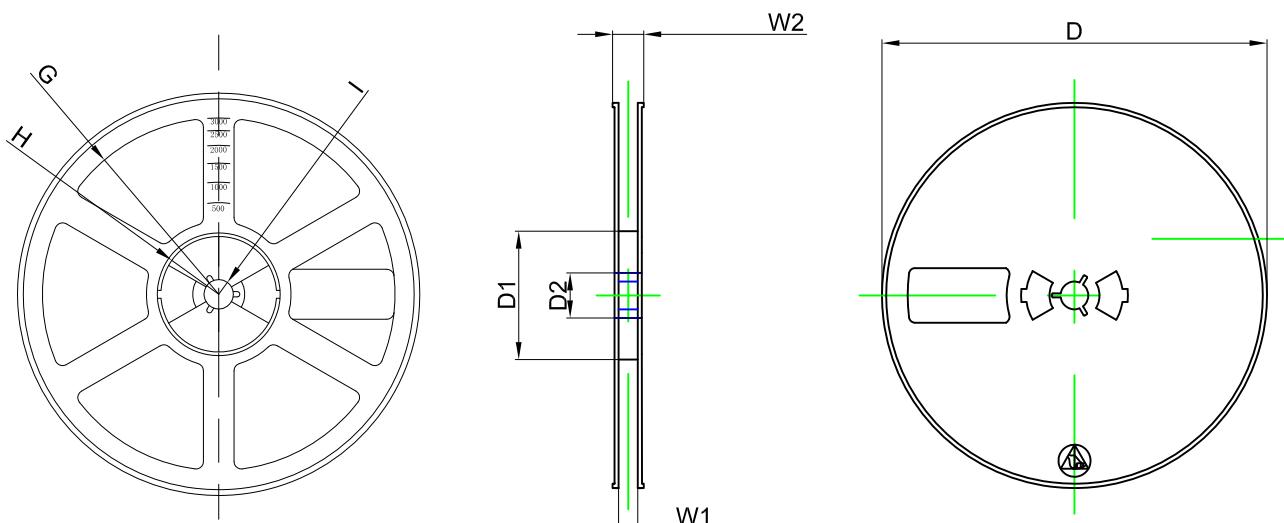
**P-Channel Enhancement Mode Power MOSFET**
**Package Information**

DFN2X2-6L


**Device Orientation in Tape**


**DFN2×2-6L Tape and Reel**
**P-Channel Enhancement Mode Power MOSFET**
**DFN2×2-6L Embossed Carrier Tape**


Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
DFN2×2-6L	2.30	2.30	1.10	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

**DFN2×2-6L Tape Leader and Trailer**

**DFN2×2-6L Reel**


Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø180.00	60.00	13.00	R78.00	R25.60	R6.50	9.50	13.10

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	

[service@jy-electronics.com.cn](mailto:service@jy-electronics.com.cn)